



HIGH DIRECTIVITY

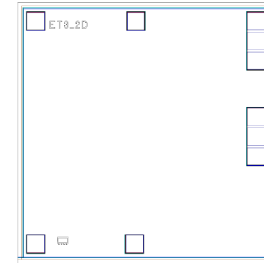
Monolithic Amplifier Die

MNA-2A-D+

50Ω 0.5 to 4.5 GHz

THE BIG DEAL

- Choice of supply voltage, +2.8V to +5V
- Internal DC blocking at RF input and output
- High directivity, +21 dB typ.
- Output power, +17.5 dBm typ.



+RoHS Compliant
 The +Suffix identifies RoHS Compliance.
 See our website for methodologies and qualifications

SEE ORDERING INFORMATION ON THE LAST PAGE

APPLICATIONS

- Buffer amplifier
- Cellular infrastructure
- Communications satellite
- Defense

PRODUCT OVERVIEW

MNA-2A-D+ is a wideband PHEMT based MMIC amplifier die with high active Directivity. MNA integrates the entire matching network and majority of the bias circuit inside the die, reducing the need for complicated external circuits. This approach makes the MNA amplifier die extremely straightforward to use. This design operates on a single 2.8 to 5V supply, is well matched for 50Ω. [MNA series models are available in Die and packaged form.](#)

KEY FEATURES

Features	Advantages
Excellent Active Directivity (Isolation- Gain) 21-36 dB	Ideal for use as a buffer amplifier minimizing interaction of adjacent circuits
Integrates DC blocks and RF choke	Minimizes external components, component count and circuit area.
Single +2.8 to +5V operation	Amplifier can be used at low voltage such as +3V or standard +5V. +5V operation results in higher P1dB and OIP3.
Unpackaged die	Enables the user to integrate the amplifier directly into hybrids.

REV. B
 ECO-015296
 MNA-2A-D+
 MCL NY
 221005





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ELECTRICAL SPECIFICATIONS¹ AT 25°C

Parameter	Condition (GHz)	Min.	Vs=5V Typ.	Max.	Vs=2.8V Typ.	Units
Frequency Range		0.5		4.5	0.5-4.5	GHz
Gain	0.5		14.1		12.4	dB
	1.0		15.0		13.0	
	2.0		15.0		12.6	
	2.5		14.7		12.3	
	3.5		12.8		10.6	
	4.5		9.7		7.8	
Input Return Loss	0.5		8		8	dB
	1.0		16		17	
	2.0		19		22	
	2.5		17		19	
	3.5		14		14	
	4.5		9		9	
Output Return Loss	0.5		14		13	dB
	1.0		21		18	
	2.0		15		18	
	2.5		14		17	
	3.5		15		19	
	4.5		17		17	
Output Power at P1dB	0.5		19.2		10.3	dBm
	1.0		19.1		11.4	
	2.0		17.9		11.8	
	2.5		17.5		11.8	
	3.5		15.8		11.7	
	4.5		13.9		11.4	
Output IP3	0.5		32		22	dBm
	1.0		31		23	
	2.0		29		23	
	2.5		29		23	
	3.5		27		23	
	4.5		25		22	
Noise Figure	0.5		5.6		5.8	dB
	1.0		5.3		5.4	
	2.0		5.3		5.5	
	2.5		5.4		5.6	
	3.5		5.6		5.7	
	4.5		6.3		6.5	
Directivity (Isolation-Gain)	0.5		33		36	dB
	1.0		29		28	
	2.0		22		22	
	2.5		21		21	
	3.5		21		21	
	4.5		24		23	
DC Current			84	104	79	mA
Device Current Variation vs. Temperature ²			32		15	μA/°C
Device Current Variation vs Voltage			0.0013		0.0034	mA/mV
Thermal resistance at 85°C (Junction to Lead)			54		54	°C/W

1. Measured on Mini-Circuits characterization test board. Die packaged in 3x3 mm MCLP package and soldered on test board TB-186+

2. (Current at 85°C - Current at -45°C)/1.30

3. (Current at 5.25V - Current at 3.9V)/1.35

4. (Current at 3.9V - Current at 2.66V)/1.24





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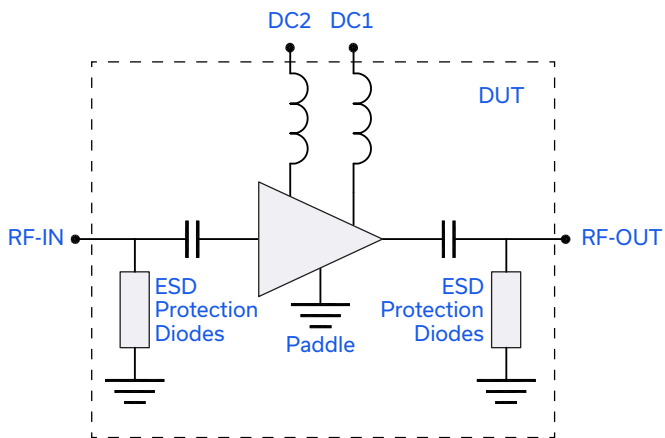
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MAXIMUM RATINGS^{1,5}

Parameter	Ratings
Operating Temperature	-40°C to 85°C
DC Voltage	7V at DC1 (DC2 connected to DC1 via 33.2Ω) 1V at RF IN & RF OUT
Power Dissipation	800 mW
Input Power	+11 dBm at Vs=+2.8V and +16 dBm at +5V (continuous operation) +23 dBm (5 minutes max)

5. Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.

SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION



Function	Description
RF IN	RF input pad.
RF-OUT	RF output pad
DC1 & DC2	DC Supply pad. Connect DC2 to DC1 via 33.2Ω resistor

1. Bond Pad material - Gold
2. Bottom of Die - Gold plated



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CHARACTERIZATION CIRCUIT

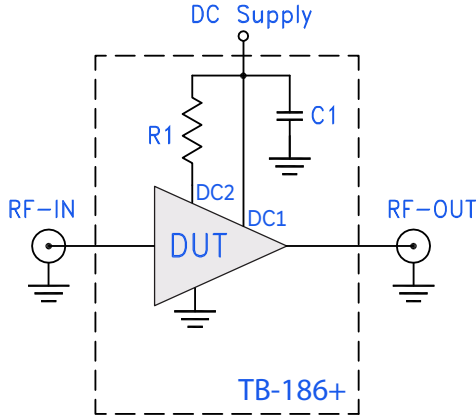


Fig 1. Block Diagram of Test Circuit used for characterization. (Die packaged in 3x3 mm MCLP package and soldered on Mini-Circuits Characterization test board TB-186+) Gain, Return loss, Output power at 1dB compression (P1 dB) , output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.

Component	Size	Value	Units
R1	0805	33.2	Ω
C1	0402	1000	ρF

RECOMMENDED APPLICATION CIRCUIT

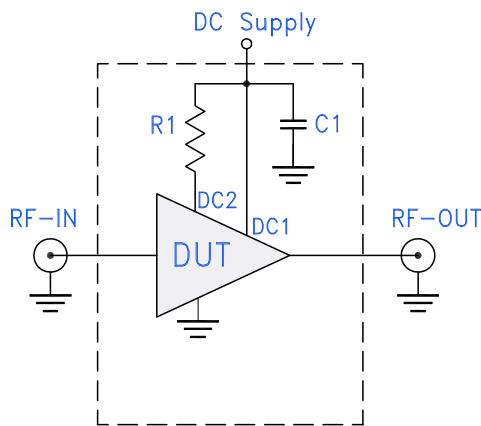


Fig 2. Test Board includes case, connectors, and components soldered to PCB

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R1	0805	33.2	Ω
C1	0402	1000	ρF



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DIE LAYOUT

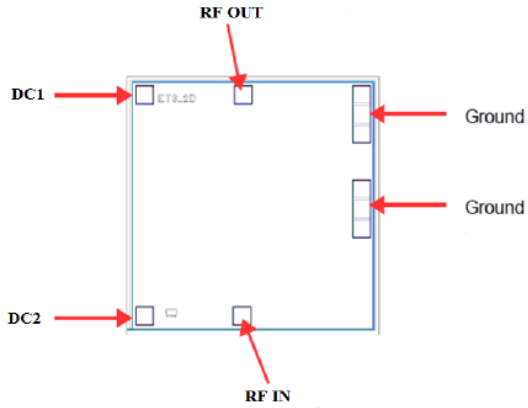


Fig 3. Die Layout

BONDING PAD POSITION

(Dimensions in μm , Typical)

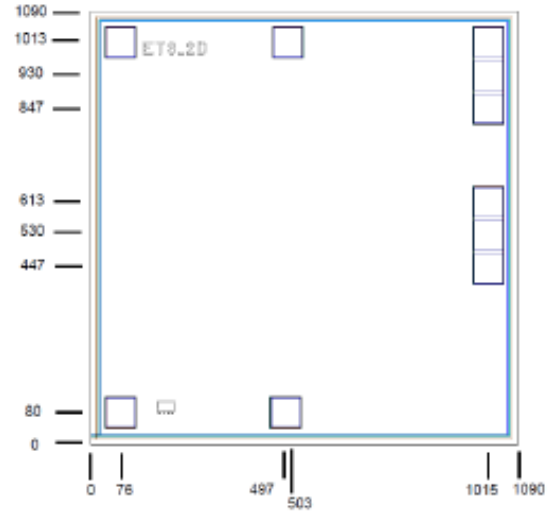


Fig 4. Bonding Pad Positions

CRITICAL DIMENSIONS

Parameter	Values
Die Thickness, μm	100
Die Width, μm	1090
Die Length, μm	1090
Bond Pad Size (RF In, RF Out, DC), μm	80 x 80
Bond Pad Size (Ground pad), μm	80 x 246



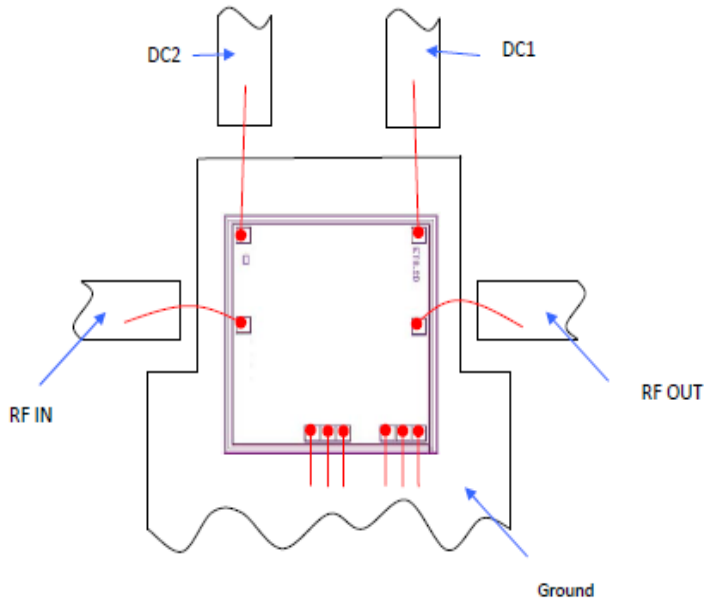
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ASSEMBLY DIAGRAM




Note: Ground bond wires are optional.

RECOMMENDED WIRE LENGTH, TYPICAL

Wire	Wire Length (mm)	Wire Loop Height (mm)
RF In, RF Out	1.20	0.15
DC	0.60	0.15
Ground	0.35	0.15

ASSEMBLY PROCEDURE

- Storage**
Die should be stored in a dry nitrogen purged desiccators or equivalent.
-  **ESD**
MMIC PHEMT amplifier Die are susceptible to electrostatic and mechanical damage. Die are supplied in antistatic protected material, which should be open in clean room conditions at an appropriately grounded anti-static workstation.
- Die Handling and Attachment**
Devices need careful handling using correctly designed collets, it is recommended to handle the chip along the edges with a custom design collet. The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are Ablestik 84-1 LMISR4 or equivalents. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. The surface of the chip has exposed air bridges and should not be touched with vacuum collet, tweezers or fingers.
- Wire Bonding**
Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the Die gold bond pads. Thermo-sonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1mil diameter. Bonds must be made from the bond pads on the die to the packaged or substrate. All bond wire length and bond wire height should be kept as short as possible unless specified by the Assembly Drawing to minimize performance degradation due to undesirable series inductance.



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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASH BOARD.

Performance Data	Data Table Swept Graphs S-Parameter (S2P Files) Data Set with and without port extension(.zip file)	
Case Style	Die	
Die Ordering and packaging information	Quantity, Package Small, Gel - Pak: 5,10,50,100 KGD* Medium†, Partial wafer: KGD*<1295 Large†, Full Wafer †Available upon request contact sales representative Refer to AN-60-067	Model No. MNA-2A-DG+ MNA-2A-DP+ MNA-2A-DF+
Environmental Ratings	ENV-80	

*Known Good Die ('KGD') means that the die in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such die fall within a predefined range. While DC testing is not definitive, it does provide a higher degree of confidence that die are capable of meeting typical RF electrical performance specified by Mini-Circuits.

ESD RATING**

Human Body Model (HBM): Class 1A (250 to < 500V) in accordance with ANSI/ESD STM 5.1 - 2001

**Tested in _x_ xxL MCLP Package

NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
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